

Supporting Information

Stable ambipolar organic-inorganic heterojunction field-effect transistors and inverters with Cytop interlayer

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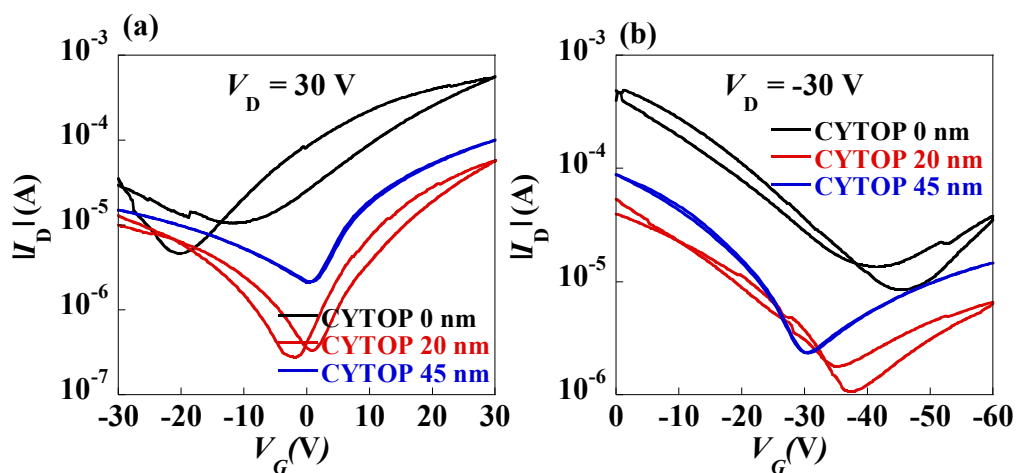


Figure S1. Transfer curves of ambipolar FETs depend on different Cytop thickness: (a) in electron enhancement mode and (b) in hole enhancement mode.

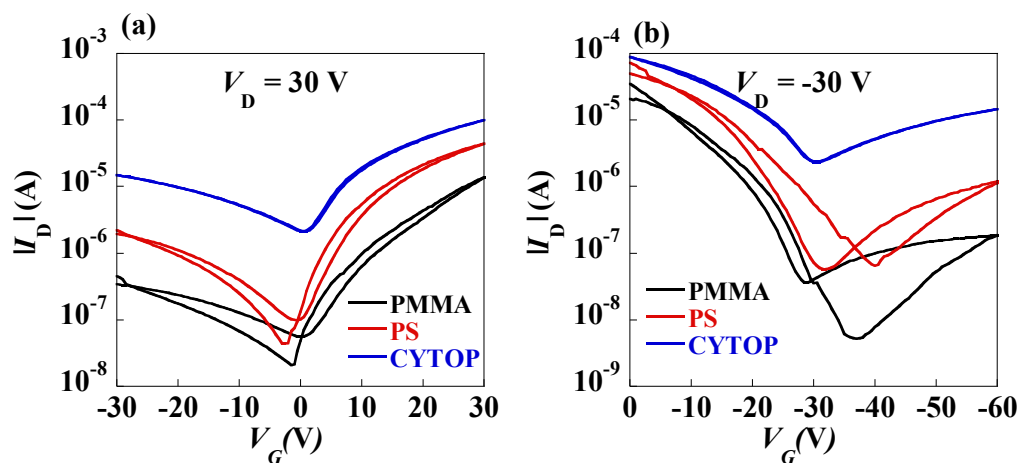


Figure S2. Transfer curves of ambipolar FETs with different modification layer (PMMA, PS or Cytop): (a) in electron enhancement mode and (b) in electron enhancement mode.

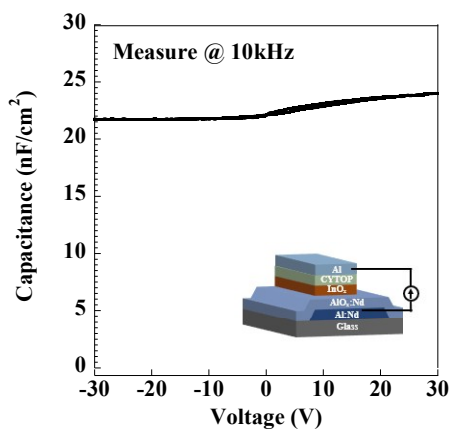


Figure S3. Capacitance vs. gate voltage plots measured at 10kHz for $\text{AlO}_x\text{:Nd}/\text{InO}_x/\text{Cytop}$; inset: the structures of the capacitance.